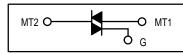
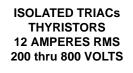
Triacs Silicon Bidirectional Thyristors

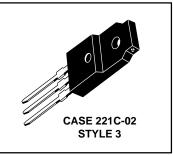
... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity
 and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC212FP Series) or Four Modes (MAC212AFP Series)



MAC212FP Series MAC212AFP Series





MAXIMUM RATINGS (T_J = 25° C unless otherwise noted.)

Rating	Rating Symbol		Unit	
Repetitive Peak Off-State Voltage ⁽¹⁾ ($T_J = -40$ to +125°C, 1/2 Sine Wave 50 to 60 Hz, Gate Open)	V _{DRM}		Volts	
MAC212-4FP, MAC212A4FP MAC212-6FP, MAC212A6FP MAC212-8FP, MAC212A8FP MAC212-10FP, MAC212A10FP		200 400 600 800		
On-State RMS Current (T _C = +85°C) Full Cycle Sine Wave 50 to 60 Hz ⁽²⁾	I _{T(RMS)}	12	Amps	
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, T _C = +85°C) preceded and followed by rated current	ITSM	100	Amps	
Circuit Fusing (t = 8.3 ms)	l ² t	40	A ² s	
Peak Gate Power (T _C = +85°C, Pulse Width = 10 μ s)	PGM	20	Watts	
Average Gate Power (T _C = +85°C, t = 8.3 ms)	PG(AV)	0.35	Watt	
Peak Gate Current (T _C = +85°C, Pulse Width = 10 μ s)	I _{GM}	2	Amps	
RMS Isolation Voltage (T _A = 25°C, Relative Humidity \leq 20%)	V(ISO)	1500	Volts	
Operating Junction Temperature	Тј	-40 to +125	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	2.1	°C/W
Thermal Resistance, Case to Sink	R _{0CS}	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	60	°C/W

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.



MAC212FP Series MAC212AFP Series

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current (Either Direction) (V _D = Rated V _{DRM} , Gate Open) $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	IDRM		_	10 2	μA mA
Peak On-State Voltage (Either Direction) (I_{TM} = 17 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle \leq 2%)	V™	-	1.3	1.75	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms, Minimum Gate Pulse Width = 2 μ s) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	IGT	 	12 12 20 35	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms, Minimum Gate Pulse Width = 2 μ s) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY (Main Terminal Voltage = Rated V _{DRM} , $R_L = 10 \text{ k}\Omega$, $T_J = +125^{\circ}\text{C}$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A " SUFFIX ONLY	VGT	 0.2 0.2	0.9 0.9 1.1 1.4 	2 2 2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 500 mA)	Чн	-	6	50	mA
Turn-On Time (V _D = Rated V _{DRM} , I _{TM} = 17 A, I _{GT} = 120 mA, Rise Time = 0.1 μ s, Pulse Width = 2 μ s)	tgt	_	1.5		μs
Critical Rate of Rise of Commutation Voltage (V _D = Rated V _{DRM} , I_{TM} = 17 A, Commutating di/dt = 6.1 A/ms, Gate Unenergized, T _C = +85°C)	dv/dt _(c)	—	5		V/µs
Critical Rate of Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Voltage Rise, Gate Open, T _C = +85°C)	dv/dt	_	100		V/µs



TYPICAL CHARACTERISTICS

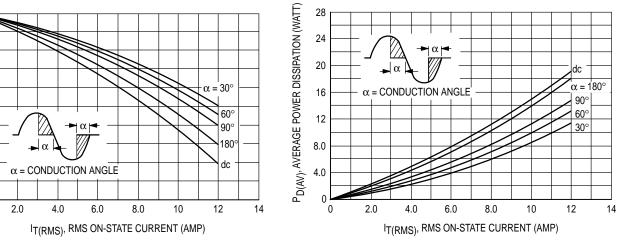


Figure 1. Current Derating

Figure 2. Power Dissipation

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MAC212FP Series MAC212AFP Series

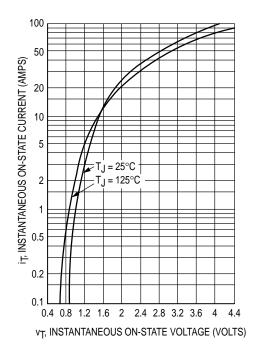


Figure 3. Maximum On-State Characteristics

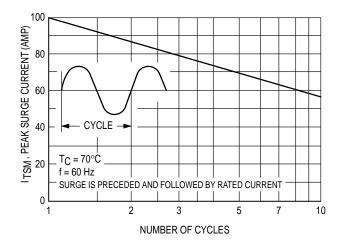


Figure 4. Maximum Nonrepetitive Surge Current

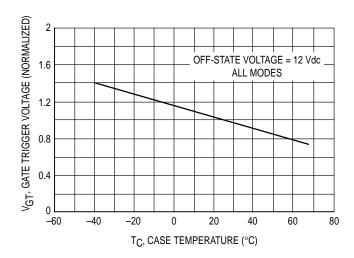


Figure 5. Typical Gate Trigger Voltage

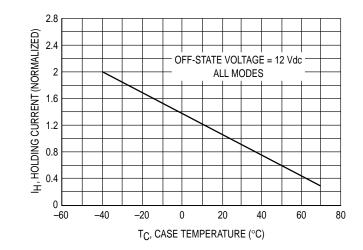


Figure 7. Typical Holding Current

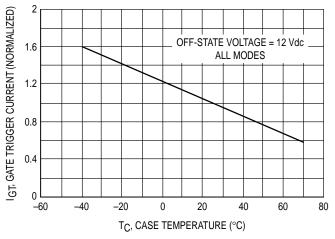


Figure 6. Typical Gate Trigger Current

MAC212FP Series MAC212AFP Series

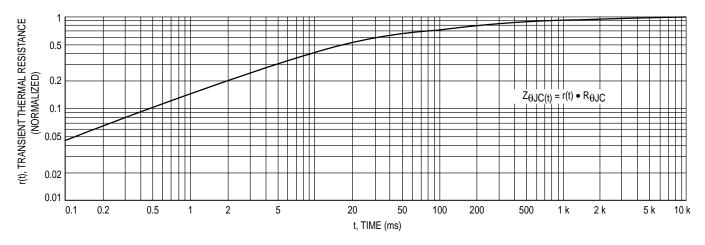
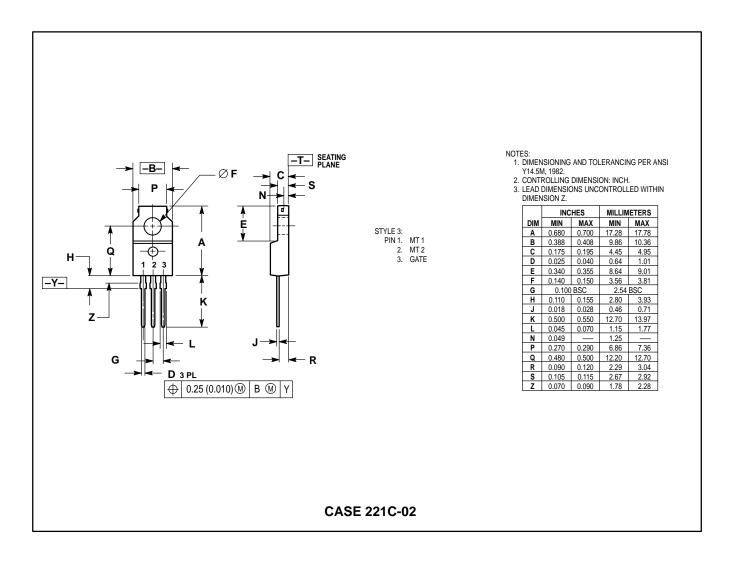


Figure 8. Thermal Response

PACKAGE DIMENSIONS



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